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013654284 \*\*Image available\*\*  
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**Apparatus for etching silicon substrate, comprises inductively coupled plasma source, reactor and magnetic field coil**

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Patent Family:

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WO 200106540	A1	20010125	WO 2000DE1836	A	20000606	200114 B
DE 19933841	A1	20010201	DE 1033841	A	19990720	200114
EP 1203396	A1	20020508	EP 2000949075	A	20000606	200238
			WO 2000DE1836	A	20000606	
KR 2002010737	A	20020204	KR 2002700719	A	20020118	200254
JP 2003505869	W	20030212	WO 2000DE1836	A	20000606	200321
			JP 2001511712	A	20000606	

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Abstract (Basic): WO 200106540 A1

NOVELTY - Apparatus for etching a substrate (10) has an inductively coupled plasma (ICP) source (13) for generating a high frequency electromagnetic alternating field, and a reactor (15) for producing an inductively coupled plasma (14) made of reactive particles by subjecting the alternating field to a reactive gas. A magnetic field coil (21) is provided which produces a static or temporarily variable magnetic field between the substrate and the ICP source.

DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for a process for etching a substrate using the above apparatus.

USE - For etching silicon bodies.

ADVANTAGE - The magnetic field is orientated in such a way that its direction is approximately or substantially parallel to the direction defined by the connecting line of the substrate and the inductively coupled plasma.

DESCRIPTION OF DRAWING(S) - The drawing shows a cross-section through the etching apparatus.

substrate (10)

ICP source (13)

inductively coupled plasma (14)

reactor (15)  
magnetic field coil (21)  
pp; 48 DwgNo 1/4

Title Terms: APPARATUS; ETCH; SILICON; SUBSTRATE; COMPRISE; INDUCTIVE;  
COUPLE; PLASMA; SOURCE; REACTOR; MAGNETIC; FIELD; COIL

Derwent Class: L03; U11; V05; X14

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